

MICRO ELECTRONICS

M2012Y HIGH BRIGHTNESS AMBER SURFACE LIGHTING

FEATURES:

- GaAsP/GaP Amber Chip
- Amber Diffused Lens
- Low Power Requirements
- Wide Viewing Angle

ABSOLUTE MAXIMUM RATINGS

(Ta=25°C)

Power dissipation/Chip	Pd	60mW
Continuous Forward Current/Chip	IF	20mA
Peak Forward Current/Chip (*Pulse Width = 1ms , Duty Ratio = 1/10)	*IFP	100mA
Reverse Voltage	VR	5V
Operating Temperature Range	Topr	-20 to +80°C
Storage Temperature Range	Tstg	-25 to +85°C
Solder Temperature (1/16 Inch from body)		260°C
Maximum Soldering Time(≤260°C)		5 sec

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

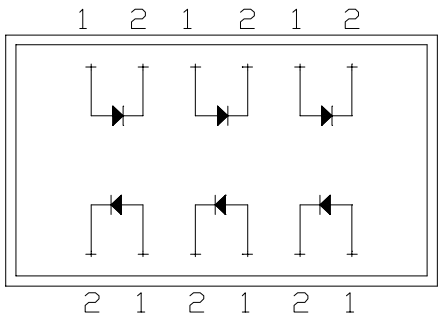
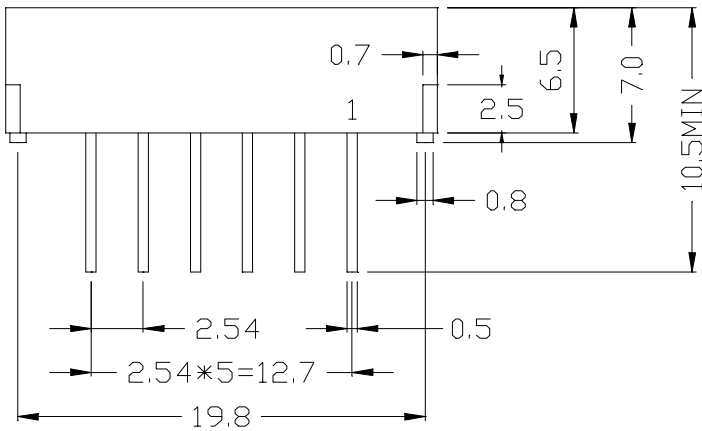
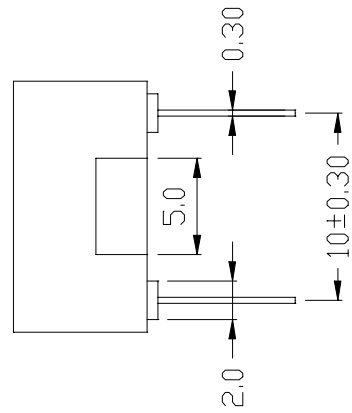
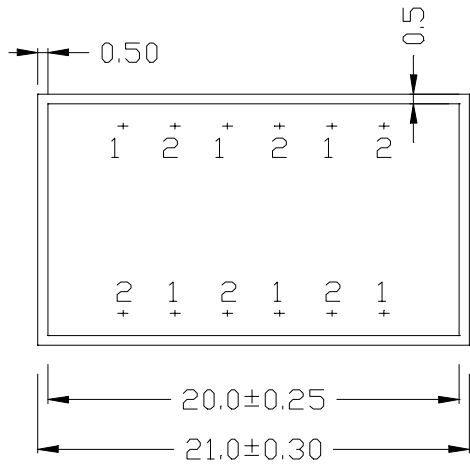
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Forward Voltage/Chip	V _F		2.1	2.8	V	I _F =20mA
Reverse Current/Chip	I _R			100	μA	V _R =5V
Peak Wavelength	λ _p		589		nm	I _F =20mA
Dominant Wavelength	λ _d		590		nm	I _F =20mA
Spectral Line Half Width	Δλ		35		nm	I _F =20mA
Luminous Intensity	IV	5	15		mcd	I _F =10mA/Chip



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M2012Y



Pin connection :
 1: Anode
 2: Cathode

Unit : mm
 Tol. : ±0.3mm unless otherwise noted